

Features

- Trench Power MV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low R_{DS(ON)}
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

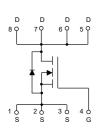
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 46°C/W Junction to Ambient(Note 2)
- Thermal Resistance: 1.67°C/W Junction to Case

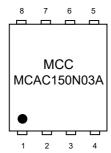
Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		150	Α	
	T _C =100°C	- I _D	95		
Pulsed Drain Current (Note 3)	I _{DM}	300	Α		
Total Power Dissipation(Note 4)		P _D	75	W	
Single Pulsed Avalanche Energy ^(Note 5)		E _{AS}	400	mJ	

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation PDSM is based on $R_{\theta JA}$ t≤10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. Pd is based on max. junction temperature, using junction-case thermal resistance.
- 5. V_{DD} =30V, V_{G} =10V, L=2mH.

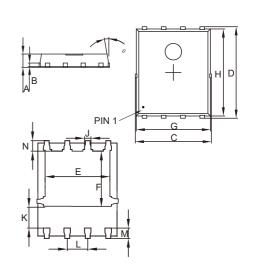
Internal Structure and Marking Code





N-CHANNEL MOSFET

DFN5060



DIMENSIONS					
DIM INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOIL
Α	0.031	0.047	0.80	1.20	
В	0.010		0.254		TYP.
С	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
Н	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.5	2.5	V	
Drain Cauras On Basistanas		V _{GS} =10V, I _D =20A		1.5	2	mΩ	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		2.4	3		
Gate Resistance	R_g	f=1MHz, Open drain		2.9		Ω	
Diode Characteristics			'				
Continuous Body Diode Current	Is				150	А	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =20A			1.2	V	
Reverse Recovery Time	t _{rr}	L 004 E/H 4004/		48		ns	
Reverse Recovery Charge	Q _{rr}	I _S =20A,di/dt=100A/µs		46		nC	
Dynamic Characteristics			·				
Input Capacitance	C _{iss}			4758			
Output Capacitance	C _{oss}	V_{DS} =15V, V_{GS} =0V,f=1MHz		757		pF	
Reverse Transfer Capacitance	C _{rss}			697			
Total Gate Charge	Qg			101			
Gate-Source Charge	Q _{gs}	V _{DS} =15V,V _{GS} =10V,I _D =20A		12		nC	
Gate-Drain Charge	Q_{gd}			25			
Turn-On Delay Time	t _{d(on)}			11			
Turn-On Rise Time	t _r	V_{DD} =15V, V_{GS} =10V, R_G =3 Ω , I_D =20A		35			
Turn-Off Delay Time	t _{d(off)}	11G-012, ID-20M		90		- ns -	
Turn-Off Fall Time	t _f			62			



Curve Characteristics

Fig. 1 - Typical Output Characteristics

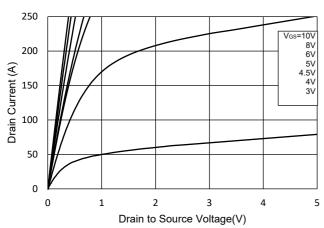


Fig.2 Transfer Characteristic

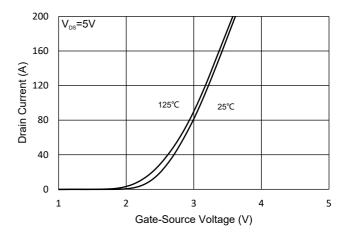


Fig.3 Rdson-Vgs

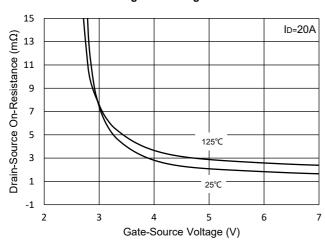


Fig.4 RDS(ON)-ID

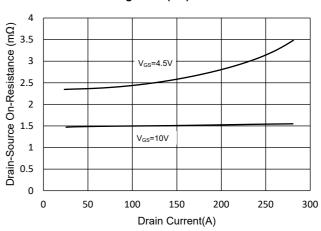


Fig.5 Capacitance Characteristics

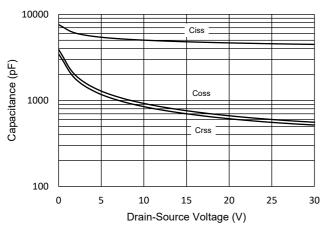
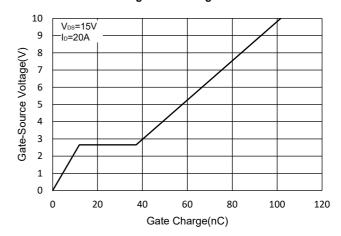
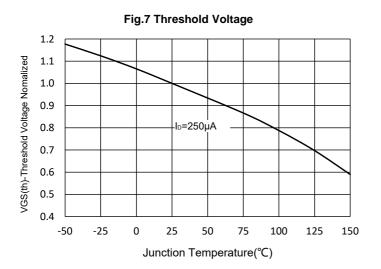


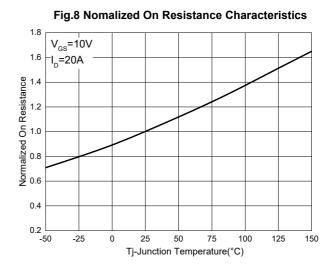
Fig.6 Gate Charge

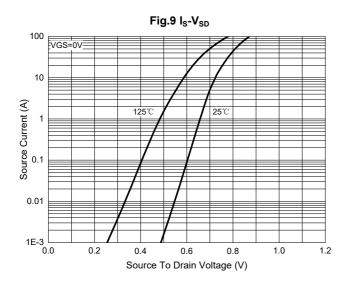


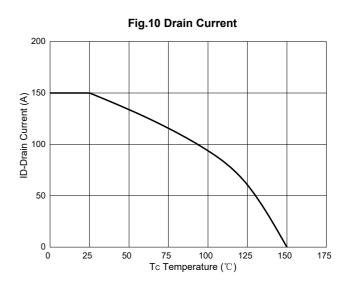


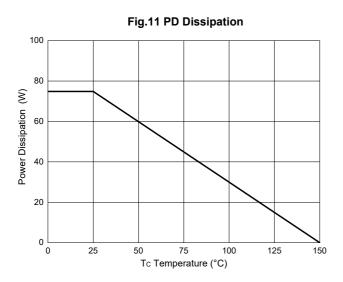
Curve Characteristics













Curve Characteristics

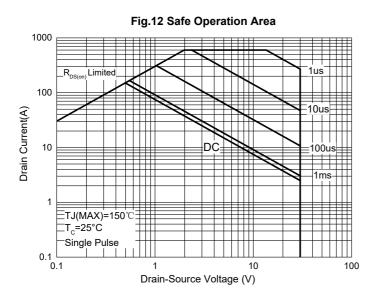
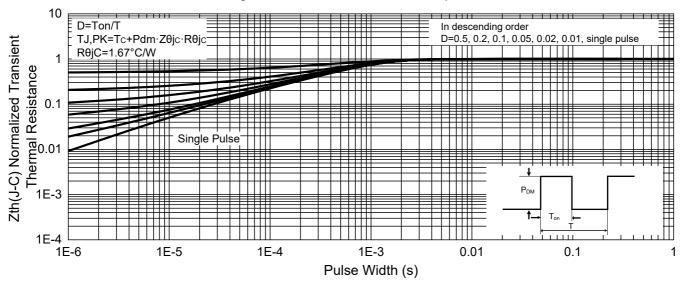


Fig.13 Normalized Transient Thermal Impedance





Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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